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PATENT

IN THE UNITED STATES PATENT  
AND TRADEMARK OFFICE

Applicants: Dae-wook Hong	)	I hereby certify that this paper is being
	)	deposited with the United States Postal
Serial No.: 10/801,407	)	Service with sufficient postage as first
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Filed: March 16, 2004	)	Mail Stop Amendment, Commissioner for
	)	Patents, P.O. Box 1450, Alexandria,
Title: METHOD FOR	)	Virginia 22313-1450, on <b>January 20,</b>
MANUFACTURING A BIPOLAR	)	<b>2006.</b>
TRANSISTOR USING A CMOS	)	
PROCESS	)	
	)	
Group Art Unit: 2822	)	
	)	
Examiner: Michael Manh Trinh	)	
	)	Sandip H. Patel (Reg. No. 43,848)
Attorney Docket No.: 29925/39911	)	Attorney for Applicants

RESPONSE PURSUANT TO 37 CFR § 1.143

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Dear Sir:

This paper is being presented pursuant to 37 CFR § 1.143 and in response to an official action dated December 20, 2005, wherein pending claims 1-10 were subjected to a two-way restriction requirement. Specifically, the action defines the restriction by the following groups:

Group I: claims 1-5 are "drawn to a first method of making a bipolar device, which method includes forming an Nbase and Pbase and forming a logic N well and P well (Fig 6a), classified in class 438;" and,

Group II: claims 6-10 are "drawn to "a second method of making a bipolar device, which method includes forming a poly gate and sequentially forming an Nbase/Pbase (Fig 6b), classified in class 438."

See the Action at p. 2. The restriction requirement is traversed, and reconsideration and withdrawal of the restriction requirement are respectfully requested in view of the following remarks.